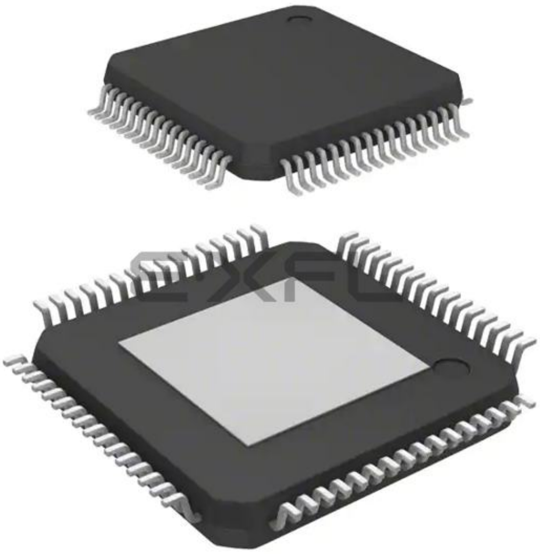
Infineon Technologies - XE162FN16F80LAAFXUMA1 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	C166SV2
Core Size	16-Bit
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I²C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I²S, POR, PWM, WDT
Number of I/O	40
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	18K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-64-6
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/xe162fn16f80laafxuma1

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For example 8 Kbytes of PSRAM will be allocated at E0’0000h-E0’1FFFh and 8 Kbytes of DSRAM will be at 00’C000h-00’DFFFh.

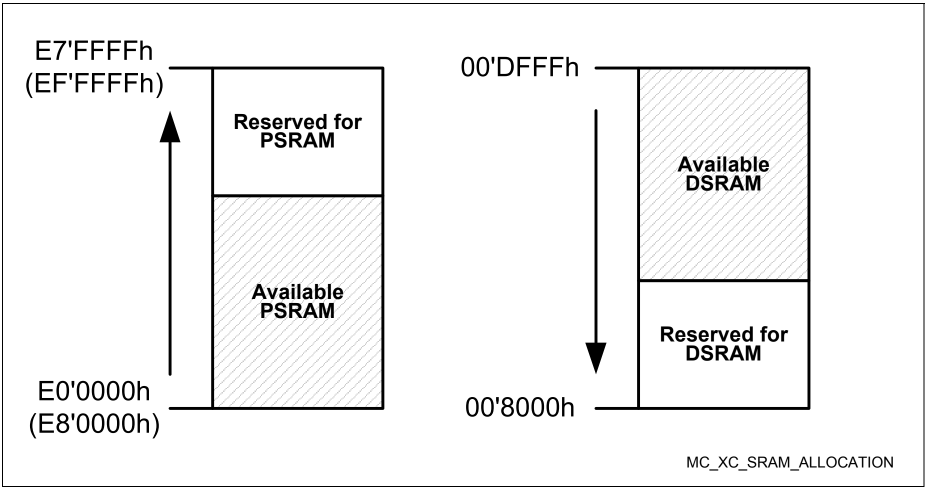

Figure 1 SRAM Allocation

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
47	P10.7	O0 / I	St/B	**Bit 7 of Port 10, General Purpose Input/Output**
	U0C1_DOUT	O1	St/B	**USIC0 Channel 1 Shift Data Output**
	CCU60_COUT63	O2	St/B	**CCU60 Channel 3 Output**
	U0C1_DX0B	I	St/B	**USIC0 Channel 1 Shift Data Input**
	CCU60_CCPOS0A	I	St/B	**CCU60 Position Input 0**
	T4INB	I	St/B	**GPT12E Timer T4 Count/Gate Input**
51	P10.8	O0 / I	St/B	**Bit 8 of Port 10, General Purpose Input/Output**
	U0C0_MCLKOUT	O1	St/B	**USIC0 Channel 0 Master Clock Output**
	U0C1_SELO0	O2	St/B	**USIC0 Channel 1 Select/Control 0 Output**
	U2C1_DOUT	O3	St/B	**USIC2 Channel 1 Shift Data Output**
	CCU60_CCPOS1A	I	St/B	**CCU60 Position Input 1**
	U0C0_DX1C	I	St/B	**USIC0 Channel 0 Shift Clock Input**
	$\overline{\text{BRKIN}}$_B	I	St/B	**OCDS Break Signal Input**
	T3EUDB	I	St/B	**GPT12E Timer T3 External Up/Down Control Input**

With this hardware most XE162xN instructions are executed in a single machine cycle of 12.5 ns @ 80-MHz CPU clock. For example, shift and rotate instructions are always processed during one machine cycle, no matter how many bits are shifted. Also, multiplication and most MAC instructions execute in one cycle. All multiple-cycle instructions have been optimized so that they can be executed very fast; for example, a 32-/16-bit division is started within 4 cycles while the remaining cycles are executed in the background. Another pipeline optimization, the branch target prediction, eliminates the execution time of branch instructions if the prediction was correct.

The CPU has a register context consisting of up to three register banks with 16 word-wide GPRs each at its disposal. One of these register banks is physically allocated within the on-chip DPRAM area. A Context Pointer (CP) register determines the base address of the active register bank accessed by the CPU at any time. The number of these register bank copies is only restricted by the available internal RAM space. For easy parameter passing, a register bank may overlap others.

A system stack of up to 32 Kwords is provided for storage of temporary data. The system stack can be allocated to any location within the address space (preferably in the on-chip RAM area); it is accessed by the CPU with the stack pointer (SP) register. Two separate SFRs, STKOV and STKUN, are implicitly compared with the stack pointer value during each stack access to detect stack overflow or underflow.

The high performance of the CPU hardware implementation can be best utilized by the programmer with the highly efficient XE162xN instruction set. This includes the following instruction classes:

- Standard Arithmetic Instructions
- DSP-Oriented Arithmetic Instructions
- Logical Instructions
- Boolean Bit Manipulation Instructions
- Compare and Loop Control Instructions
- Shift and Rotate Instructions
- Prioritize Instruction
- Data Movement Instructions
- System Stack Instructions
- Jump and Call Instructions
- Return Instructions
- System Control Instructions
- Miscellaneous Instructions

The basic instruction length is either 2 or 4 bytes. Possible operand types are bits, bytes and words. A variety of direct, indirect or immediate addressing modes are provided to specify the required operands.

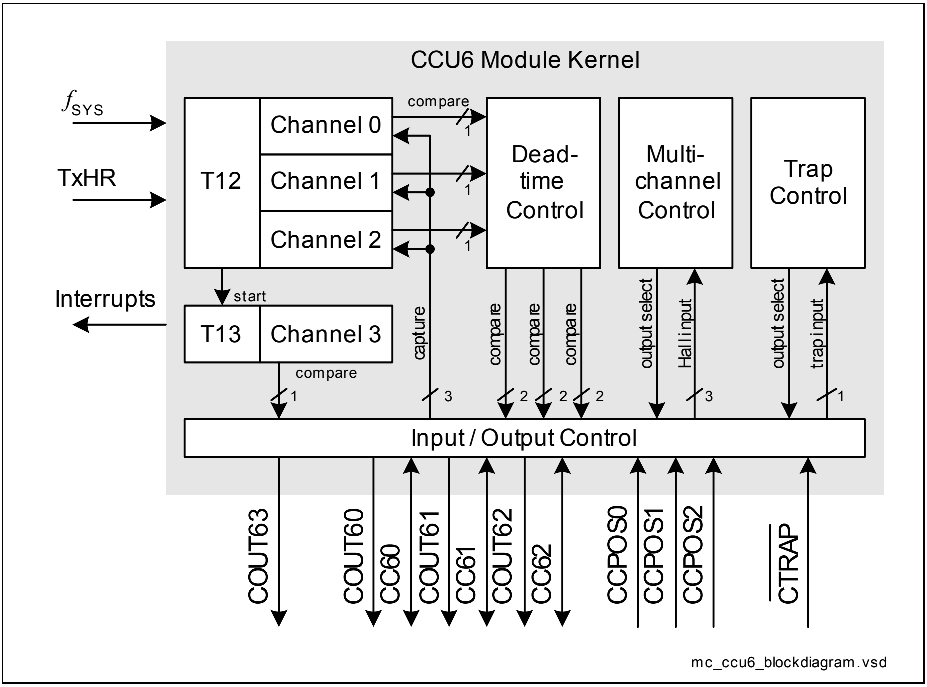

Figure 7 **CCU6 Block Diagram**

Timer T12 can work in capture and/or compare mode for its three channels. The modes can also be combined. Timer T13 can work in compare mode only. The multi-channel control unit generates output patterns that can be modulated by timer T12 and/or timer T13. The modulation sources can be selected and combined for signal modulation.

3.10 Real Time Clock

The Real Time Clock (RTC) module of the XE162xN can be clocked with a clock signal selected from internal sources or external sources (pins).

The RTC basically consists of a chain of divider blocks:

- Selectable 32:1 and 8:1 dividers (on - off)
- The reloadable 16-bit timer T14
- The 32-bit RTC timer block (accessible via registers RTCH and RTCL) consisting of:
  - a reloadable 10-bit timer
  - a reloadable 6-bit timer
  - a reloadable 6-bit timer
  - a reloadable 10-bit timer

All timers count up. Each timer can generate an interrupt request. All requests are combined to a common node request.

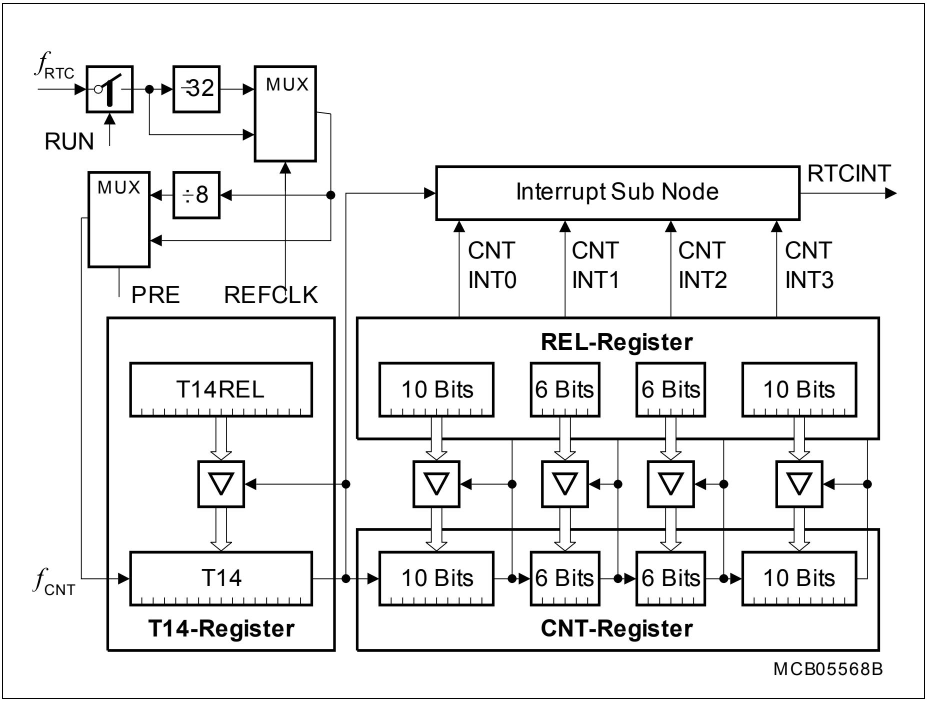

Figure 10 RTC Block Diagram

Note: The registers associated with the RTC are only affected by a power reset.

3.12 Universal Serial Interface Channel Modules (USIC)

The XE162xN features the USIC modules USIC0, USIC1, USIC2. Each module provides two serial communication channels.

The Universal Serial Interface Channel (USIC) module is based on a generic data shift and data storage structure which is identical for all supported serial communication protocols. Each channel supports complete full-duplex operation with a basic data buffer structure (one transmit buffer and two receive buffer stages). In addition, the data handling software can use FIFOs.

The protocol part (generation of shift clock/data/control signals) is independent of the general part and is handled by protocol-specific preprocessors (PPPs).

The USIC's input/output lines are connected to pins by a pin routing unit. The inputs and outputs of each USIC channel can be assigned to different interface pins, providing great flexibility to the application software. All assignments can be made during runtime.

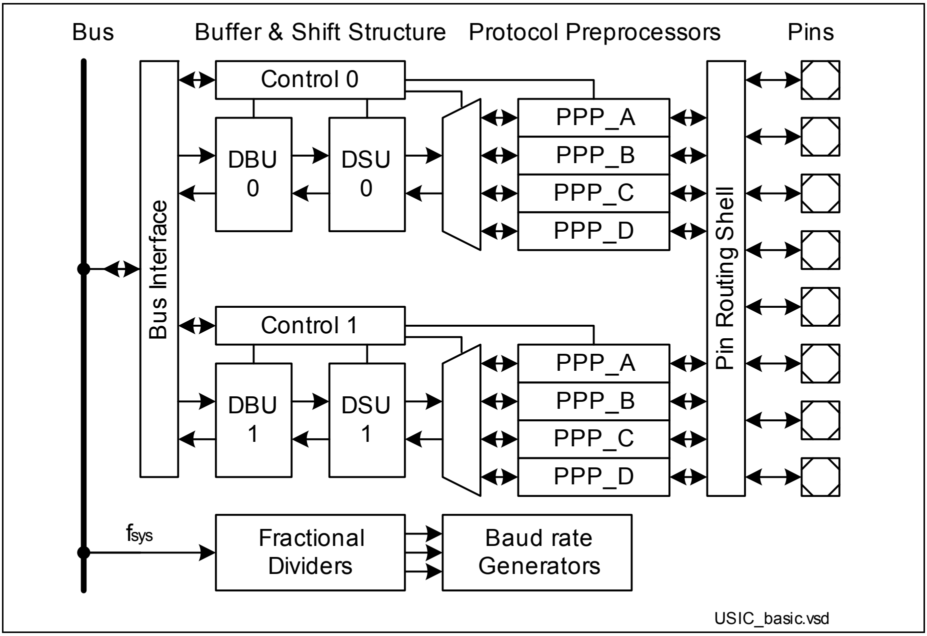

Figure 11 General Structure of a USIC Module

The regular structure of the USIC module brings the following advantages:

- Higher flexibility through configuration with same look-and-feel for data management
- Reduced complexity for low-level drivers serving different protocols
- Wide range of protocols with improved performances (baud rate, buffer handling)

4.1.1 Operating Conditions

The following operating conditions must not be exceeded to ensure correct operation of the XE162xN. All parameters specified in the following sections refer to these operating conditions, unless otherwise noticed.

Note: Typical parameter values refer to room temperature and nominal supply voltage, minimum/maximum parameter values also include conditions of minimum/maximum temperature and minimum/maximum supply voltage. Additional details are described where applicable.

Table 12 Operating Conditions

Parameter	**Symbol**	**Values**			**Unit**	**Note / Test Condition**
		Min.	**Typ.**	**Max.**		
Voltage Regulator Buffer Capacitance for DMP_M	C_{EVRM} SR	1.0	–	4.7	µF	[1]
Voltage Regulator Buffer Capacitance for DMP_1	C_{EVR1} SR	0.47	–	2.2	µF	[2][1]
External Load Capacitance	C_{L} SR	–	20[3]	–	pF	pin out driver= default [4]
System frequency	f_{SYS} SR	–	–	80	MHz	[5]
Overload current for analog inputs[6]	I_{OVA} SR	-2	–	5	mA	not subject to production test
Overload current for digital inputs[6]	I_{OVD} SR	-5	–	5	mA	not subject to production test
Overload current coupling factor for analog inputs[7]	K_{OVA} CC	–	2.5×10^{-4}	1.5×10^{-3}	-	$I_{\mathrm{OV}} < 0$ mA; not subject to production test
		–	1.0×10^{-6}	1.0×10^{-4}	-	$I_{\mathrm{OV}} > 0$ mA; not subject to production test

Table 15 DC Characteristics for Upper Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output High voltage[7]	V_{OH} CC	V_{DDP} - 1.0	–	–	V	$I_{OH} \geq I_{OHmax}$
		V_{DDP} - 0.4	–	–	V	$I_{OH} \geq I_{OHnom}$ [8]
Output Low Voltage[7]	V_{OL} CC	–	–	0.4	V	$I_{OL} \leq I_{OLnom}$ [8]
		–	–	1.0	V	$I_{OL} \leq I_{OLmax}$

1) Because each double bond pin is connected to two pads (standard pad and high-speed pad), it has twice the normal value. For a list of affected pins refer to the pin definitions table in chapter 2.

2) Not subject to production test - verified by design/characterization. Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It cannot suppress switching due to external system noise under all conditions.

3) If the input voltage exceeds the respective supply voltage due to ground bouncing ($V_{IN} < V_{SS}$) or supply ripple ($V_{IN} > V_{DDP}$), a certain amount of current may flow through the protection diodes. This current adds to the leakage current. An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin. Please refer to the definition of the overload coupling factor K_{OV}.

4) The given values are worst-case values. In production test, this leakage current is only tested at 125 °C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (T_J = junction temperature [°C]): $I_{OZ} = 0.05 \text{ x } e^{(1.5 + 0.028 \text{ x } TJ>)}$ [µA]. For example, at a temperature of 95 °C the resulting leakage current is 3.2 µA. Leakage derating depending on voltage level (DV = V_{DDP} - V_{PIN} [V]): $I_{OZ} = I_{OZtempmax}$ - (1.6 x DV) (µA]. This voltage derating formula is an approximation which applies for maximum temperature.

5) Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device.

6) Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level.

7) The maximum deliverable output current of a port driver depends on the selected output driver mode. This specification is not valid for outputs which are switched to open drain mode. In this case the respective output will float and the voltage is determined by the external circuit.

8) As a rule, with decreasing output current the output levels approach the respective supply level (V_{OL}->V_{SS}, V_{OH}->V_{DDP}). However, only the levels for nominal output currents are verified.

Table 16 DC Characteristics for Lower Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Output High voltage[7]	V_{OH} CC	V_{DDP} - 1.0	–	–	V	$I_{OH} \geq I_{OHmax}$
		V_{DDP} - 0.4	–	–	V	$I_{OH} \geq I_{OHnom}$ [8]
Output Low Voltage[7]	V_{OL} CC	–	–	0.4	V	$I_{OL} \leq I_{OLnom}$ [8]
		–	–	1.0	V	$I_{OL} \leq I_{OLmax}$

1) Because each double bond pin is connected to two pads (standard pad and high-speed pad), it has twice the normal value. For a list of affected pins refer to the pin definitions table in chapter 2.

2) Not subject to production test - verified by design/characterization. Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It cannot suppress switching due to external system noise under all conditions.

3) If the input voltage exceeds the respective supply voltage due to ground bouncing ($V_{IN} < V_{SS}$) or supply ripple ($V_{IN} > V_{DDP}$), a certain amount of current may flow through the protection diodes. This current adds to the leakage current. An additional error current (I_{INJ}) will flow if an overload current flows through an adjacent pin. Please refer to the definition of the overload coupling factor K_{OV}.

4) The given values are worst-case values. In production test, this leakage current is only tested at 125 °C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (T_J = junction temperature [°C]): $I_{OZ} = 0.05 \times e^{(1.5 + 0.028 \times TJ>)}$ [µA]. For example, at a temperature of 95 °C the resulting leakage current is 3.2 µA. Leakage derating depending on voltage level (DV = V_{DDP} - V_{PIN} [V]): $I_{OZ} = I_{OZtempmax} - (1.6 \times DV)$ (µA]. This voltage derating formula is an approximation which applies for maximum temperature.

5) Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device: $V_{PIN} <= V_{IL}$ for a pullup; $V_{PIN} >= V_{IH}$ for a pulldown.

6) Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level: $V_{PIN} >= V_{IH}$ for a pullup; $V_{PIN} <= V_{IL}$ for a pulldown.

7) The maximum deliverable output current of a port driver depends on the selected output driver mode. This specification is not valid for outputs which are switched to open drain mode. In this case the respective output will float and the voltage is determined by the external circuit.

8) As a rule, with decreasing output current the output levels approach the respective supply level (V_{OL}->V_{SS}, V_{OH}->V_{DDP}). However, only the levels for nominal output currents are verified.

Sample time and conversion time of the XE162xN's A/D converters are programmable. The timing above can be calculated using **Table 20**.
The limit values for f_{ADCI} must not be exceeded when selecting the prescaler value.

Table 20 A/D Converter Computation Table

GLOBCTR.5-0 (DIVA)	**A/D Converter Analog Clock f_{ADCI}**	**INPCRx.7-0 (STC)**	**Sample Time[1] t_S**
000000_B	f_{SYS}	00_H	$t_{ADCI} \times 2$
000001_B	$f_{SYS} / 2$	01_H	$t_{ADCI} \times 3$
000010_B	$f_{SYS} / 3$	02_H	$t_{ADCI} \times 4$
:	$f_{SYS} / (DIVA+1)$	:	$t_{ADCI} \times (STC+2)$
111110_B	$f_{SYS} / 63$	FE_H	$t_{ADCI} \times 256$
111111_B	$f_{SYS} / 64$	FF_H	$t_{ADCI} \times 257$

[1] The selected sample time is doubled if broken wire detection is active (due to the presampling phase).

Converter Timing Example A:

Assumptions: f_{SYS} $= 80$ MHz (i.e. $t_{SYS} = 12.5$ ns), DIVA = 03_H, STC = 00_H
Analog clock f_{ADCI} $= f_{SYS} / 4 = 20$ MHz, i.e. $t_{ADCI} = 50$ ns
Sample time t_S $= t_{ADCI} \times 2 = 100$ ns

Conversion 10-bit:

t_{C10} $= 13 \times t_{ADCI} + 2 \times t_{SYS} = 13 \times 50\text{ ns} + 2 \times 12.5\text{ ns} = 0.675\ \mu\text{s}$

Conversion 8-bit:

t_{C8} $= 11 \times t_{ADCI} + 2 \times t_{SYS} = 11 \times 50\text{ ns} + 2 \times 12.5\text{ ns} = 0.575\ \mu\text{s}$

Converter Timing Example B:

Assumptions: f_{SYS} $= 40$ MHz (i.e. $t_{SYS} = 25$ ns), DIVA = 02_H, STC = 03_H
Analog clock f_{ADCI} $= f_{SYS} / 3 = 13.3$ MHz, i.e. $t_{ADCI} = 75$ ns
Sample time t_S $= t_{ADCI} \times 5 = 375$ ns

Conversion 10-bit:

t_{C10} $= 16 \times t_{ADCI} + 2 \times t_{SYS} = 16 \times 75\text{ ns} + 2 \times 25\text{ ns} = 1.25\ \mu\text{s}$

Conversion 8-bit:

t_{C8} $= 14 \times t_{ADCI} + 2 \times t_{SYS} = 14 \times 75\text{ ns} + 2 \times 25\text{ ns} = 1.10\ \mu\text{s}$

4.6 Flash Memory Parameters

The XE162xN is delivered with all Flash sectors erased and with no protection installed.

The data retention time of the XE162xN's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 24 Flash Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Parallel Flash module program/erase limit depending on Flash read activity	N_{PP} SR	–	–	2[1]		$N_{FL\_RD} \leq 1$
		–	–	1[2]		$N_{FL\_RD} > 1$
Flash erase endurance for security pages	N_{SEC} SR	10	–	–	cycles	$t_{RET} \geq$ 20 years
Flash wait states[3]	$N_{WSFLASH}$ SR	1	–	–		$f_{SYS} \leq$ 8 MHz
		2	–	–		$f_{SYS} \leq$ 13 MHz
		3	–	–		$f_{SYS} \leq$ 17 MHz
		4	–	–		$f_{SYS} >$ 17 MHz
Erase time per sector/page	t_{ER} CC	–	7[4]	8.0	ms	
Programming time per page	t_{PR} CC	–	3[4]	3.5	ms	
Data retention time	t_{RET} CC	20	–	–	years	$N_{ER} \leq$ 1,000 cycles
Drain disturb limit	N_{DD} SR	32	–	–	cycles	
Number of erase cycles	N_{ER} SR	–	–	15.000	cycles	$t_{RET} \geq$ 5 years; Valid for Flash module 1 (up to 64 kbytes)
		–	–	1.000	cycles	$t_{RET} \geq$ 20 years

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[1] The unused Flash module(s) can be erased/programmed while code is executed and/or data is read from only one Flash module or from PSRAM. The Flash module that delivers code/data can, of course, not be erased/programmed.

4.7.2 Definition of Internal Timing

The internal operation of the XE162xN is controlled by the internal system clock f_{SYS}.

Because the system clock signal f_{SYS} can be generated from a number of internal and external sources using different mechanisms, the duration of the system clock periods (TCSs) and their variation (as well as the derived external timing) depend on the mechanism used to generate f_{SYS}. This must be considered when calculating the timing for the XE162xN.

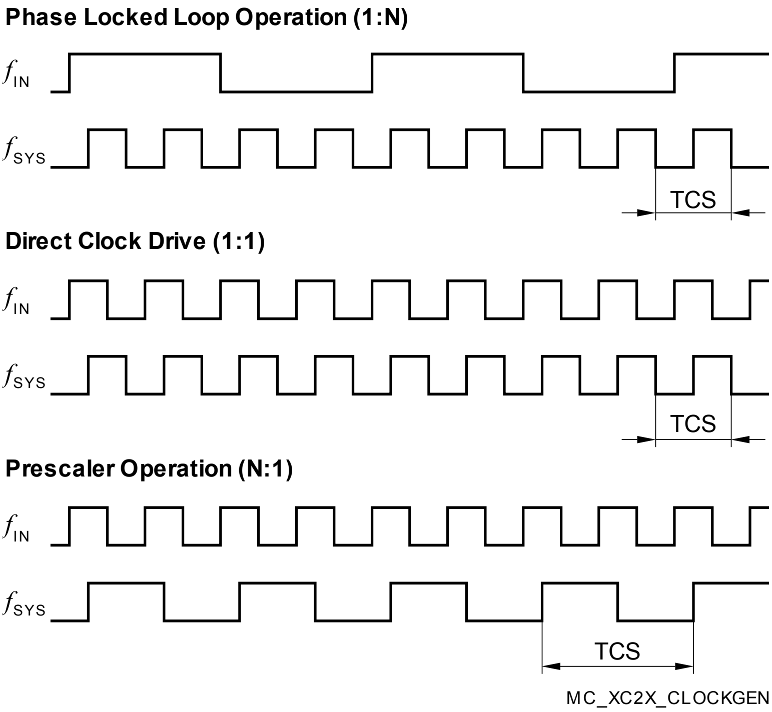

Figure 19 Generation Mechanisms for the System Clock

*Note: The example of PLL operation shown in **Figure 19** uses a PLL factor of 1:4; the example of prescaler operation uses a divider factor of 2:1.*

The specification of the external timing (AC Characteristics) depends on the period of the system clock (TCS).

Direct Drive

When direct drive operation is selected (SYSCON0.CLKSEL = 11_B), the system clock is derived directly from the input clock signal CLKIN1:

$f_{SYS} = f_{IN}$.

The frequency of f_{SYS} is the same as the frequency of f_{IN}. In this case the high and low times of f_{SYS} are determined by the duty cycle of the input clock f_{IN}.

Selecting Bypass Operation from the XTAL1[1] input and using a divider factor of 1 results in a similar configuration.

Prescaler Operation

When prescaler operation is selected (SYSCON0.CLKSEL = 10_B, PLLCON0.VCOBY = 1_B), the system clock is derived either from the crystal oscillator (input clock signal XTAL1) or from the internal clock source through the output prescaler K1 (= K1DIV+1):

$f_{SYS} = f_{OSC}$ / K1.

If a divider factor of 1 is selected, the frequency of f_{SYS} equals the frequency of f_{OSC}. In this case the high and low times of f_{SYS} are determined by the duty cycle of the input clock f_{OSC} (external or internal).

The lowest system clock frequency results from selecting the maximum value for the divider factor K1:

$f_{SYS} = f_{OSC}$ / 1024.

4.7.2.1 Phase Locked Loop (PLL)

When PLL operation is selected (SYSCON0.CLKSEL = 10_B, PLLCON0.VCOBY = 0_B), the on-chip phase locked loop is enabled and provides the system clock. The PLL multiplies the input frequency by the factor **F** ($f_{SYS} = f_{IN} \times$ **F**).
F is calculated from the input divider P (= PDIV+1), the multiplication factor N (= NDIV+1), and the output divider K2 (= K2DIV+1):
(**F** = N / (P × K2)).

The input clock can be derived either from an external source at XTAL1 or from the on-chip clock source.

The PLL circuit synchronizes the system clock to the input clock. This synchronization is performed smoothly so that the system clock frequency does not change abruptly.

Adjustment to the input clock continuously changes the frequency of f_{SYS} so that it is locked to f_{IN}. The slight variation causes a jitter of f_{SYS} which in turn affects the duration of individual TCSs.

---

1) Voltages on XTAL1 must comply to the core supply voltage V_{DDIM}.

The timing in the AC Characteristics refers to TCSs. Timing must be calculated using the minimum TCS possible under the given circumstances.
The actual minimum value for TCS depends on the jitter of the PLL. Because the PLL is constantly adjusting its output frequency to correspond to the input frequency (from crystal or oscillator), the accumulated jitter is limited. This means that the relative deviation for periods of more than one TCS is lower than for a single TCS (see formulas and **Figure 20**).

This is especially important for bus cycles using waitstates and for the operation of timers, serial interfaces, etc. For all slower operations and longer periods (e.g. pulse train generation or measurement, lower baudrates, etc.) the deviation caused by the PLL jitter is negligible.

The value of the accumulated PLL jitter depends on the number of consecutive VCO output cycles within the respective timeframe. The VCO output clock is divided by the output prescaler K2 to generate the system clock signal f_{SYS}. The number of VCO cycles is K2 × **T**, where **T** is the number of consecutive f_{SYS} cycles (TCS).

The maximum accumulated jitter (long-term jitter) D_{Tmax} is defined by:

$\mathbf{D_{Tmax}}$ **[ns] =** $\pm(220 / (K2 \times f_{SYS}) + 4.3)$

This maximum value is applicable, if either the number of clock cycles $T > (f_{SYS} / 1.2)$ or the prescaler value $K2 > 17$.

In all other cases for a timeframe of **T** × TCS the accumulated jitter D_T is determined by:

$\mathbf{D_T}$ **[ns] =** $D_{Tmax} \times [(1 - 0.058 \times K2) \times (T - 1) / (0.83 \times f_{SYS} - 1) + 0.058 \times K2]$

f_{SYS} in [MHz] in all formulas.

Example, for a period of 3 TCSs @ 33 MHz and K2 = 4:

$D_{max} = \pm(220 / (4 \times 33) + 4.3) = 5.97$ ns (Not applicable directly in this case!)

$D_3 = 5.97 \times [(1 - 0.058 \times 4) \times (3 - 1) / (0.83 \times 33 - 1) + 0.058 \times 4]$
$= 5.97 \times [0.768 \times 2 / 26.39 + 0.232]$
$= 1.7$ ns

Example, for a period of 3 TCSs @ 33 MHz and K2 = 2:

$D_{max} = \pm(220 / (2 \times 33) + 4.3) = 7.63$ ns (Not applicable directly in this case!)

$D_3 = 7.63 \times [(1 - 0.058 \times 2) \times (3 - 1) / (0.83 \times 33 - 1) + 0.058 \times 2]$
$= 7.63 \times [0.884 \times 2 / 26.39 + 0.116]$
$= 1.4$ ns

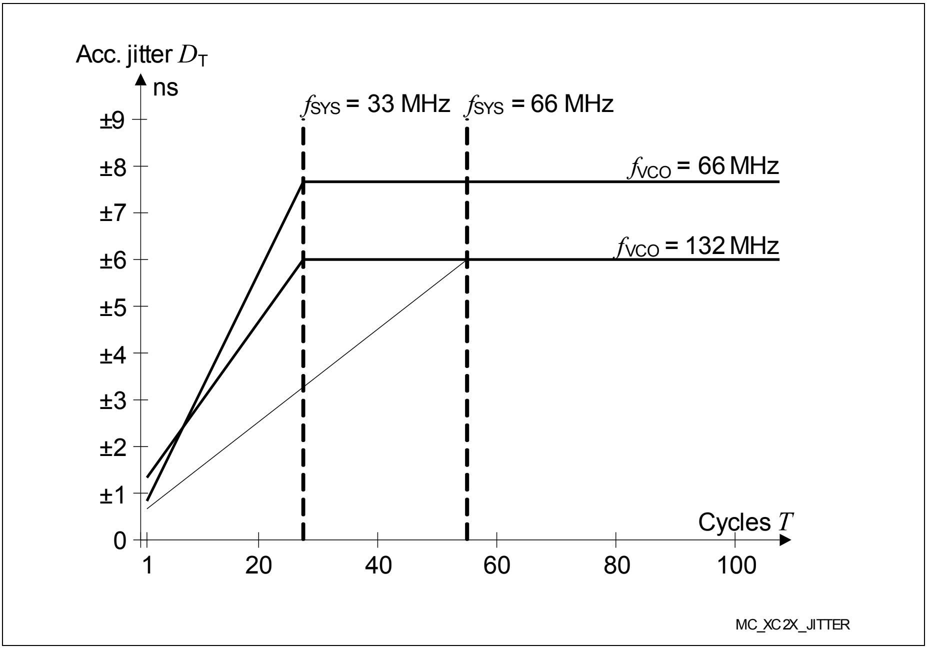

Figure 20 Approximated Accumulated PLL Jitter

Note: The specified PLL jitter values are valid if the capacitive load per pin does not exceed C_L = 20 pF.
The maximum peak-to-peak noise on the pad supply voltage (measured between V_{DDPB} pin 64 and V_{SS} pin 1) is limited to a peak-to-peak voltage of V_{PP} = 50 mV. This can be achieved by appropriate blocking of the supply voltage as close as possible to the supply pins and using PCB supply and ground planes.

PLL frequency band selection

Different frequency bands can be selected for the VCO so that the operation of the PLL can be adjusted to a wide range of input and output frequencies:

1) The amplitude voltage V_{AX1} refers to the offset voltage V_{OFF}. This offset voltage must be stable during the operation and the resulting voltage peaks must remain within the limits defined by V_{IX1}.

2) Overload conditions must not occur on pin XTAL1.

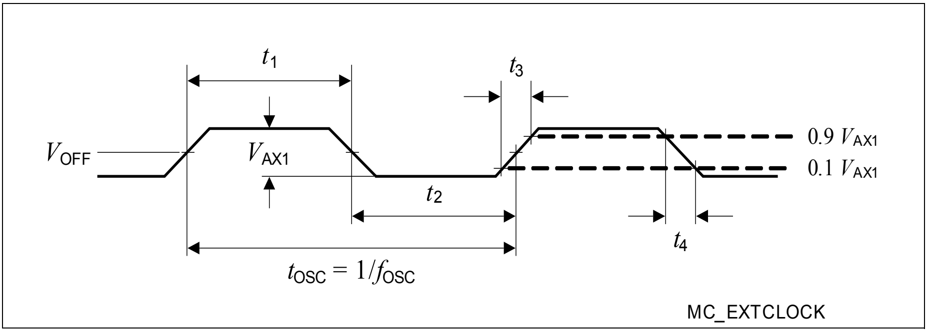

Figure 21 External Clock Drive XTAL1

Note: For crystal or ceramic resonator operation, it is strongly recommended to measure the oscillation allowance (negative resistance) in the final target system (layout) to determine the optimum parameters for oscillator operation.
The manufacturers of crystals and ceramic resonators offer an oscillator evaluation service. This evaluation checks the crystal/resonator specification limits to ensure a reliable oscillator operation.

Table 35 JTAG Interface Timing for Upper Voltage Range (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TCK low time	t_3 SR	16	–	–	ns	
TCK clock rise time	t_4 SR	–	–	8	ns	
TCK clock fall time	t_5 SR	–	–	8	ns	
TDI/TMS setup to TCK rising edge	t_6 SR	6	–	–	ns	
TDI/TMS hold after TCK rising edge	t_7 SR	6	–	–	ns	
TDO valid from TCK falling edge (propagation delay)[2]	t_8 CC	–	25	29	ns	
TDO high impedance to valid output from TCK falling edge[3][2]	t_9 CC	–	25	29	ns	
TDO valid output to high impedance from TCK falling edge[2]	t_{10} CC	–	25	29	ns	
TDO hold after TCK falling edge[2]	t_{18} CC	5	–	–	ns	

1) Under typical conditions, the JTAG interface can operate at transfer rates up to 20 MHz.

2) The falling edge on TCK is used to generate the TDO timing.

3) The setup time for TDO is given implicitly by the TCK cycle time.

Table 36 is valid under the following conditions: C_L= 20 pF; voltage_range= lower

Table 36 JTAG Interface Timing for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TCK clock period	t_1 SR	50	–	–	ns	
TCK high time	t_2 SR	16	–	–	ns	
TCK low time	t_3 SR	16	–	–	ns	
TCK clock rise time	t_4 SR	–	–	8	ns	
TCK clock fall time	t_5 SR	–	–	8	ns	
TDI/TMS setup to TCK rising edge	t_6 SR	6	–	–	ns	

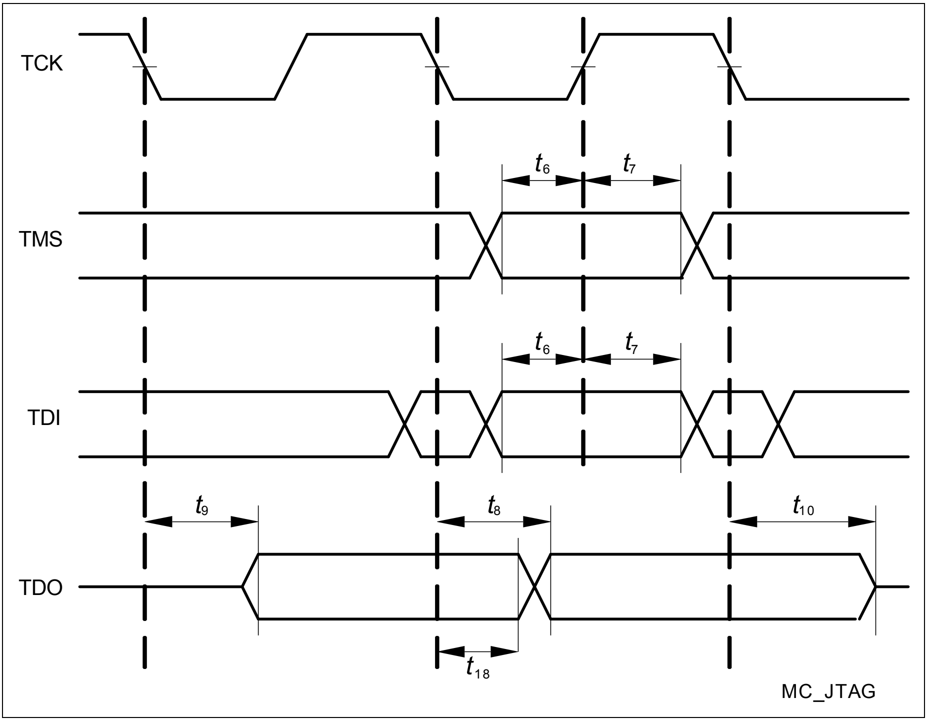

Figure 27 JTAG Timing

Package Outlines

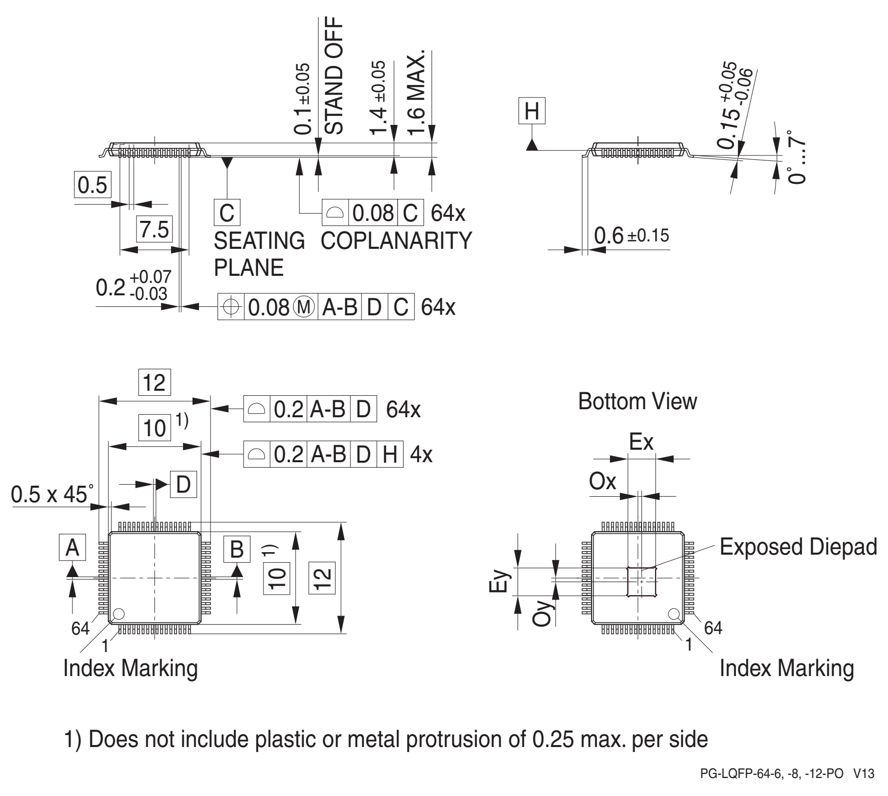

Figure 28 PG-LQFP-64-6 (Plastic Green Thin Quad Flat Package)

All dimensions in mm.

You can find complete information about Infineon packages, packing and marking in our Infineon Internet Page “Packages”: **http://www.infineon.com/packages**